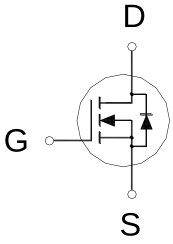
NIKO-SEM

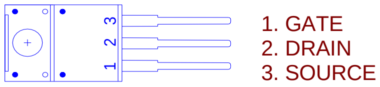
N-Channel Enhancement Mode Field Effect Transistor

P0470ETF:TO-220F
P0470ETFS:TO-220FS
Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
700V	2.8Ω	4A





ABSOLUTE MAXIMUN RATINGS(T_A=25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	700	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current[2]	T_C = 25 °C	I_D	4	A
	T_C = 100 °C		2.6	
Pulsed Drain Current[1]		I_{DM}	16	
Avalanche Current[3]		IAS	2	
Avalanche Energy[3]		EAS	20	mJ
Power Dissipation	T_C = 25 °C	P_D	54	W
	T_C = 100 °C		22	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.3	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	°C / W

[1] Pulse width limited by maximum junction temperature.
[2] Ensure that the channel temperature does not exceed 150°C.
[3] V_{DD} = 50V , L = 10mH ,starting T_J = 25°C.

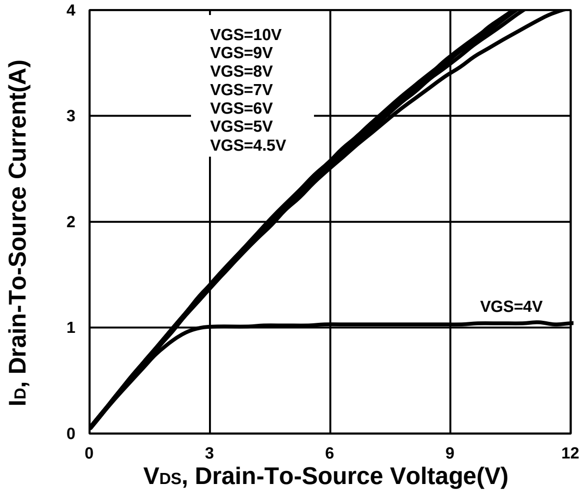
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	700			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3	4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±30V			±100	nA

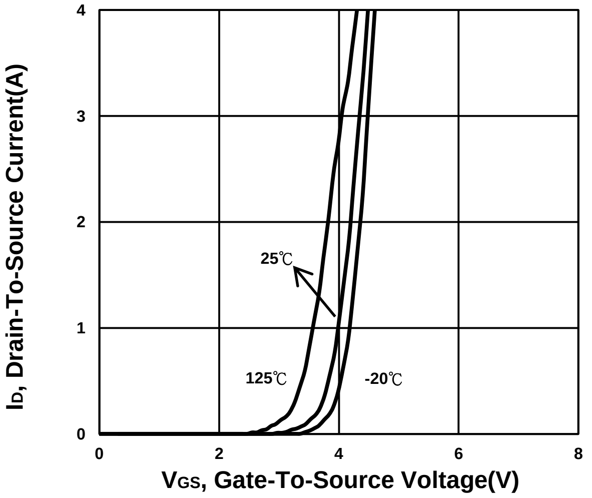
Gate Voltage Drain Current	I_{DSS}	V_{DS} = 700V, V_{GS} = 0V , T_C = 25 °C			1	µA
		V_{DS} = 560V, V_{GS} = 0V , T_C = 100 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 2A		2.2	2.8	Ω
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 2A		7.7		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		661		pF
Output Capacitance	C_{oss}			63		
Reverse Transfer Capacitance	C_{rss}			8		
Total Gate Charge[2]	Q_g	V_{DD} = 560V, I_D =4A, V_{GS} = 10V		14		nC
Gate-Source Charge[2]	Q_{gs}			2.9		
Gate-Drain Charge[2]	Q_{gd}			3.2		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 350V, I_D =4A, R_G= 6Ω		37		nS
Rise Time[2]	t_r			13.5		
Turn-Off Delay Time[2]	$t_{d(off)}$			17		
Fall Time[2]	t_f			12.3		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				4	A
Forward Voltage[1]	V_{SD}	I_F =4A, V_{GS} = 0V			1	V
Reverse Recovery Time	t_{rr}	I_F =4A, dI_F/dt = 100A / µS		354		nS
Reverse Recovery Charge	Q_{rr}			2.4		uC

[1] Pulse test : Pulse Width ≤ 380 µsec, Duty Cycle ≤ 2%.
[2] Independent of operating temperature.
[3] Pulse width limited by maximum junction temperature.

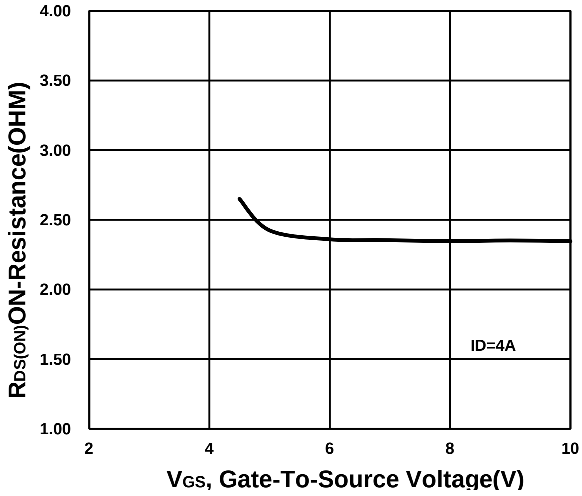
Output Characteristics



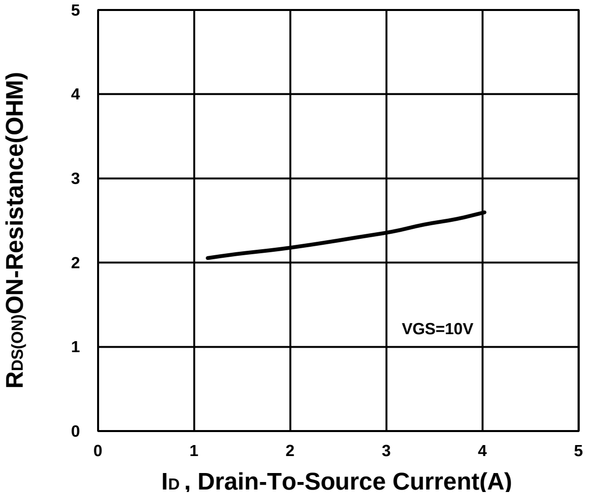
Transfer Characteristics



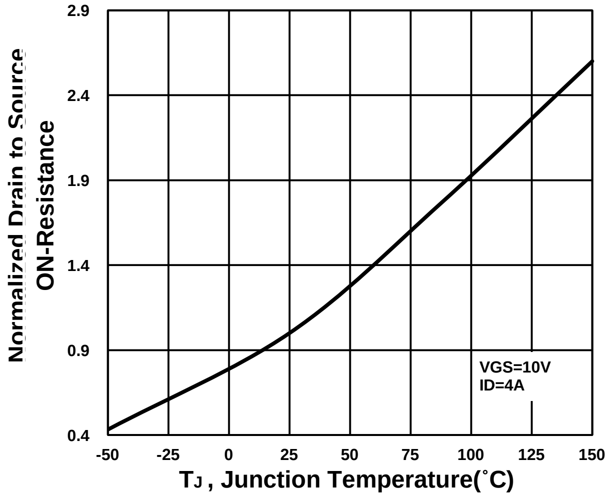
On-Resistance VS Gate-To-Source



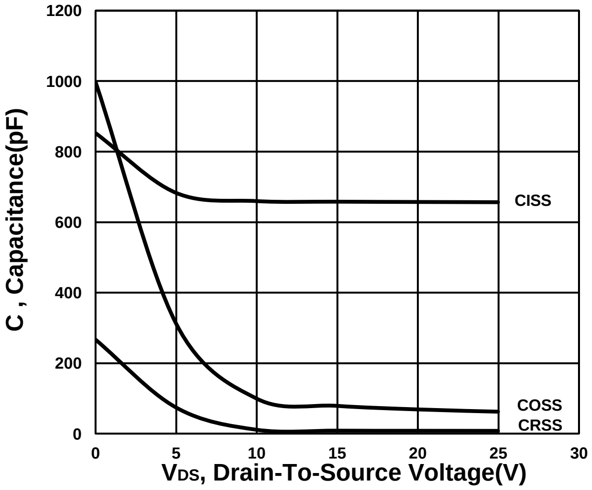
On-Resistance VS Drain Current

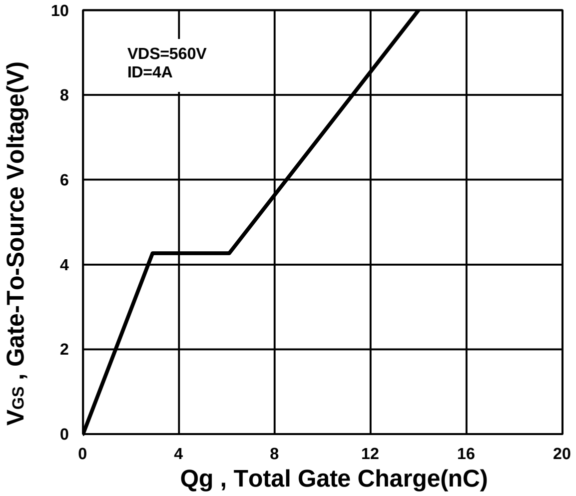


On-Resistance VS Temperature

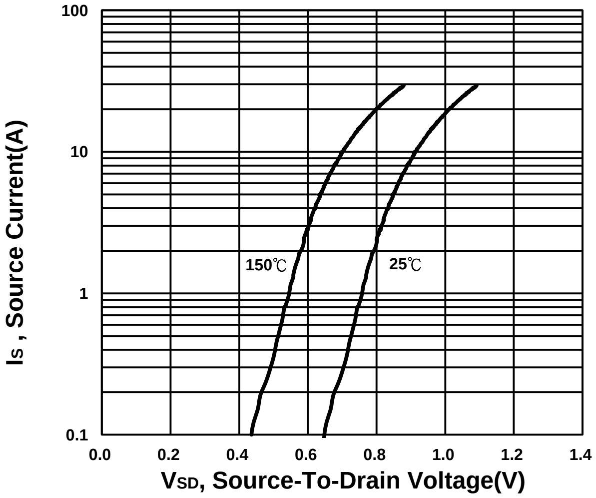


Capacitance Characteristic

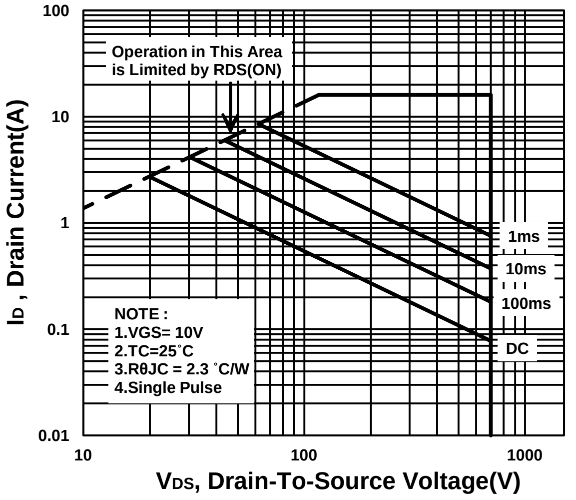




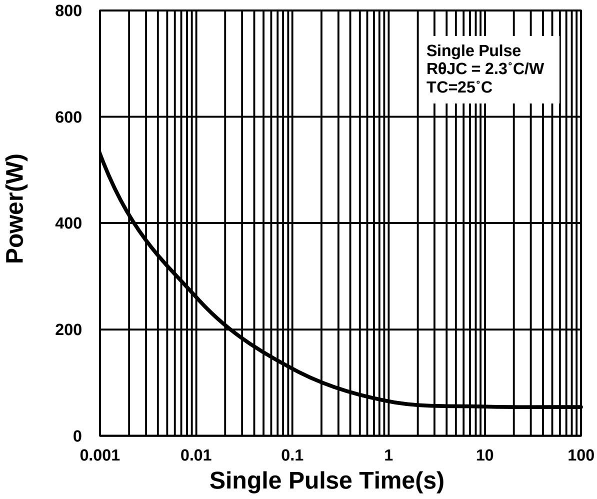
Gate charge Characteristics



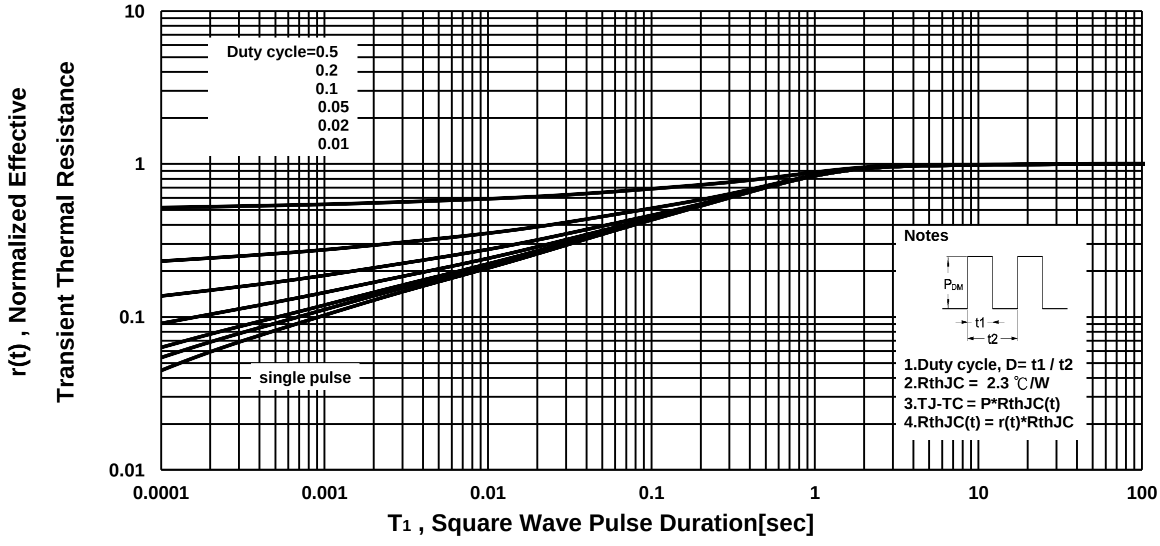
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve